

2SA561 is PNP silicon planar transistor designed for low power general purpose amplifiers.

TO-92B



ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	50V
Collector-Emitter Voltage	VCEO	50V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	150mA
Total Power Dissipation	Ptot	300mW
Operating Junction & Storage Temperature	Tj, Tstg	-55 to +150°C

ECB

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS	
Collector-Emitter Breakdown Voltage	LVCEO	50		V	IC=10mA IB=0	
Collector Cutoff Current	ICBO		100	nA	VCB=18V IE=0	
Emitter Cutoff Current	IEBO		100	nA	VEB=5V IC=0	
D.C. Current Gain	HFE	All group	70	400	V	IC=20mA VCE=1V
		Group O	70	140		
		Group Y	120	240		
		Group GR	200	400		
		All group	23			
		Group O	23			
		Group Y	40			
		Group GR	67			
Collector-Emitter Saturation Voltage	VCE(sat)		0.3	V	IC=100mA IB=10mA*	
Current Gain Bandwidth Product	fT	70	TYP	MHz	IC=1mA VCE=6V	
Output Capacitance	Cob	13	TYP	pF	VCB=6V f=1MHz	

\* Pulse Test : Pulse Width <300us, duty cycle <2%.



MICRO ELECTRONICS LTD. 美科有限公司 FAX: 3-410321

38 Hung To Road, Kwun Tong, Kowloon, Hong Kong. Cable: Microtron, Hong Kong. Telex: 43510 Micro Hx.  
P.O. Box 69477, Kwun Tong. Tel: 3-430181-6, 3-893363, 3-892423, 3-898224

M B P